



**ALPHA & OMEGA**  
SEMICONDUCTOR, LTD

**AO8814**

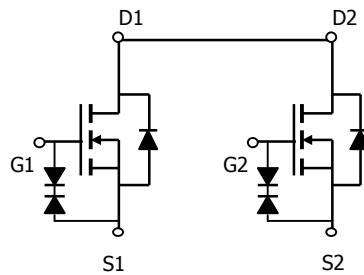
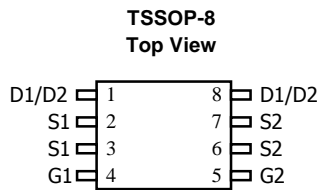
**Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO8814 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V  $V_{GS(MAX)}$  rating. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

**Features**

- $V_{DS}$  (V) = 20V
- $I_D = 7.5$  A ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 16m\Omega$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 18m\Omega$  ( $V_{GS} = 4.5V$ )
- $R_{DS(ON)} < 20m\Omega$  ( $V_{GS} = 3.6V$ )
- $R_{DS(ON)} < 24m\Omega$  ( $V_{GS} = 2.5V$ )
- $R_{DS(ON)} < 34m\Omega$  ( $V_{GS} = 1.8V$ )
- ESD Rating: 2500V HBM



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10s$	64	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	83	
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	53	70	$^\circ\text{C/W}$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	20			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 10\text{V}$			10	$\mu\text{A}$
$BV_{GSO}$	Gate-Source Breakdown Voltage	$V_{DS}=0\text{V}$ , $I_G=\pm 250\mu\text{A}$	$\pm 12$			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.5	0.71	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=7.5\text{A}$ $T_J=125^\circ\text{C}$	10	13	16	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=7\text{A}$	11.5	15	18	
		$V_{GS}=3.6\text{V}$ , $I_D=6\text{A}$	13	16.8	20	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=6\text{A}$	15	19	24	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}$ , $I_D=5\text{A}$	20	26	34	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=7.5\text{A}$		30		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.74	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=10\text{V}$ , $f=1\text{MHz}$		1390		pF
$C_{oss}$	Output Capacitance			190		pF
$C_{rss}$	Reverse Transfer Capacitance			150		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.5		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=10\text{V}$ , $I_D=7.5\text{A}$		15.4		nC
$Q_{gs}$	Gate Source Charge			1.4		nC
$Q_{gd}$	Gate Drain Charge			4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=5\text{V}$ , $V_{DS}=10\text{V}$ , $R_L=1.3\Omega$ , $R_{GEN}=3\Omega$		6.2		ns
$t_r$	Turn-On Rise Time			11		ns
$t_{D(off)}$	Turn-Off DelayTime			40.5		ns
$t_f$	Turn-Off Fall Time			10		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=7.5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		15		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=7.5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		5.1		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

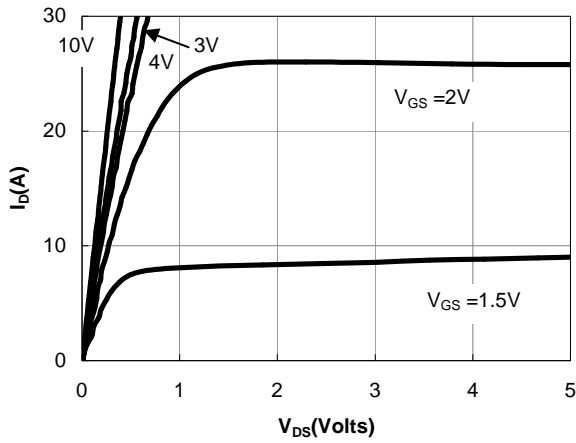


Figure 1: On-Regions Characteristics

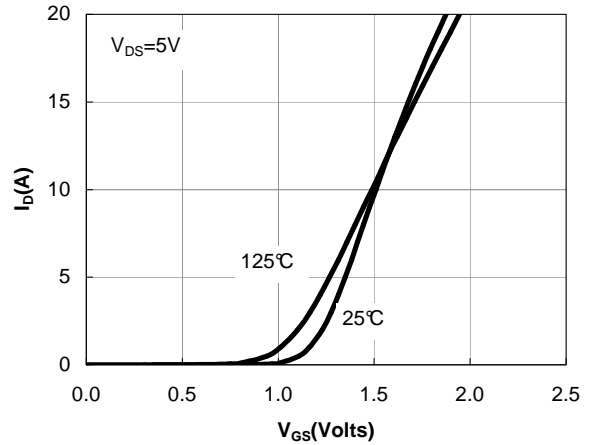


Figure 2: Transfer Characteristics

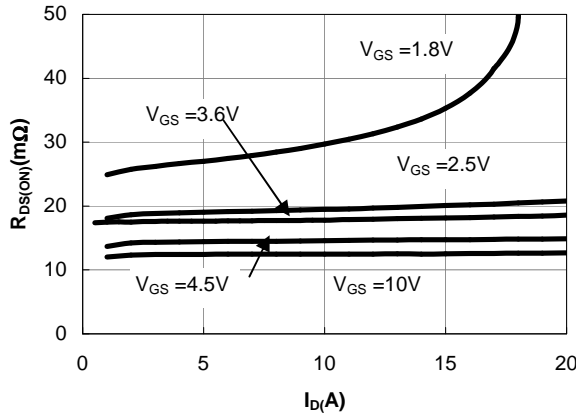


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

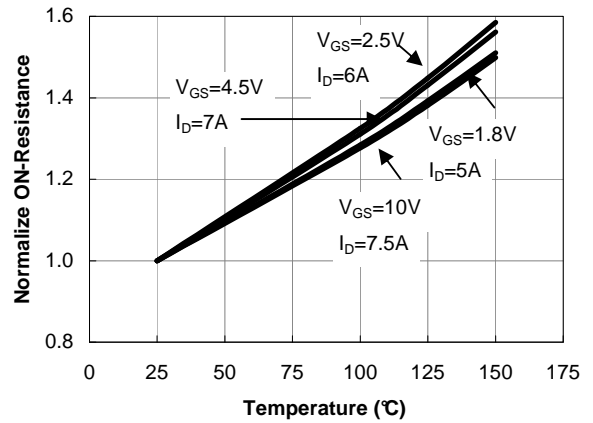


Figure 4: On-Resistance vs. Junction Temperature

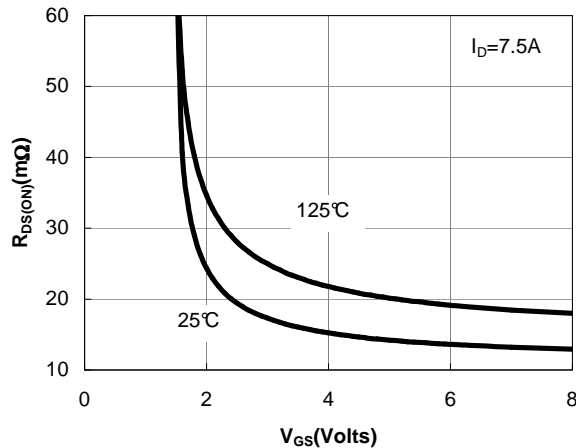


Figure 5: On-Resistance vs. Gate-Source Voltage

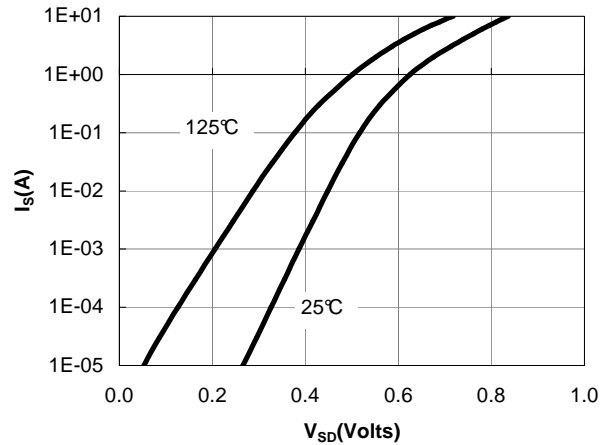


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

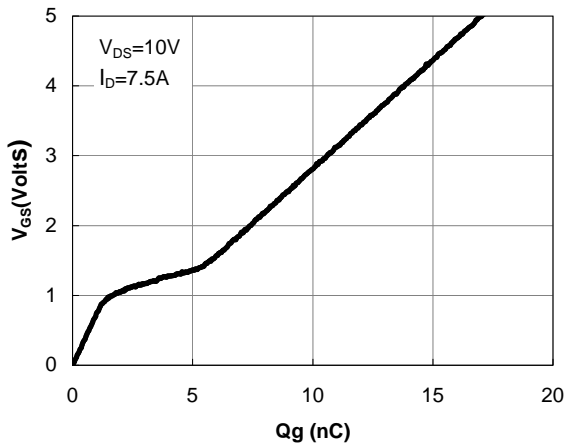


Figure 7: Gate-Charge Characteristics

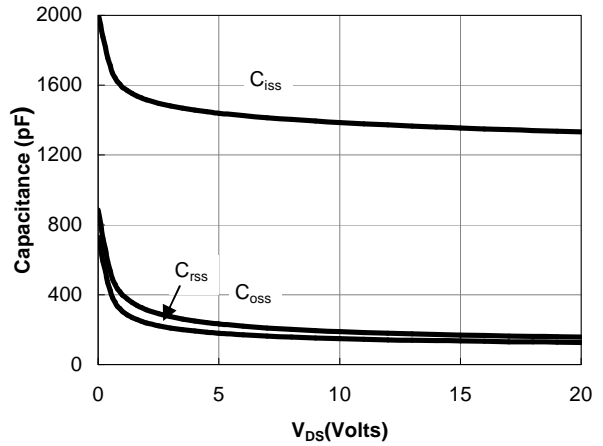


Figure 8: Capacitance Characteristics

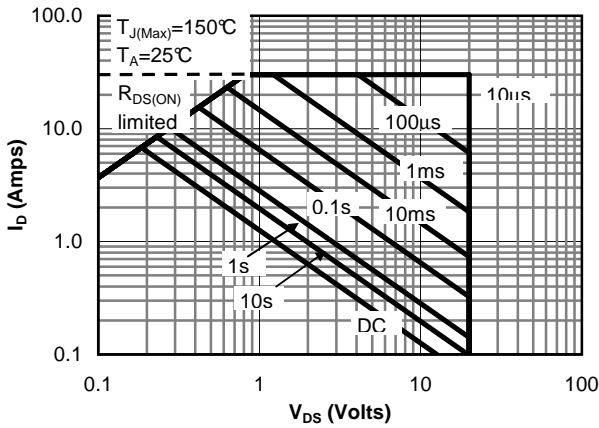


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

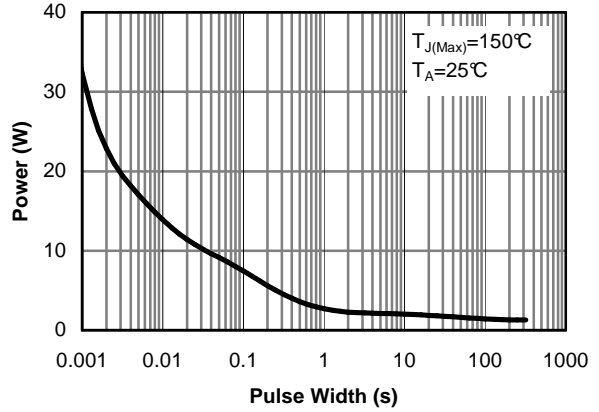


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

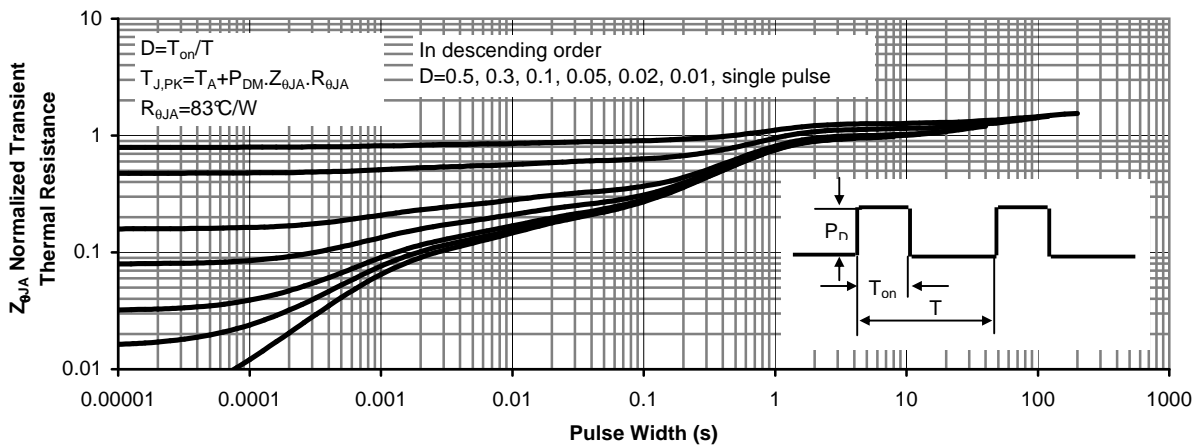


Figure 11: Normalized Maximum Transient Thermal Impedance

单击下面可查看定价，库存，交付和生命周期等信息

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